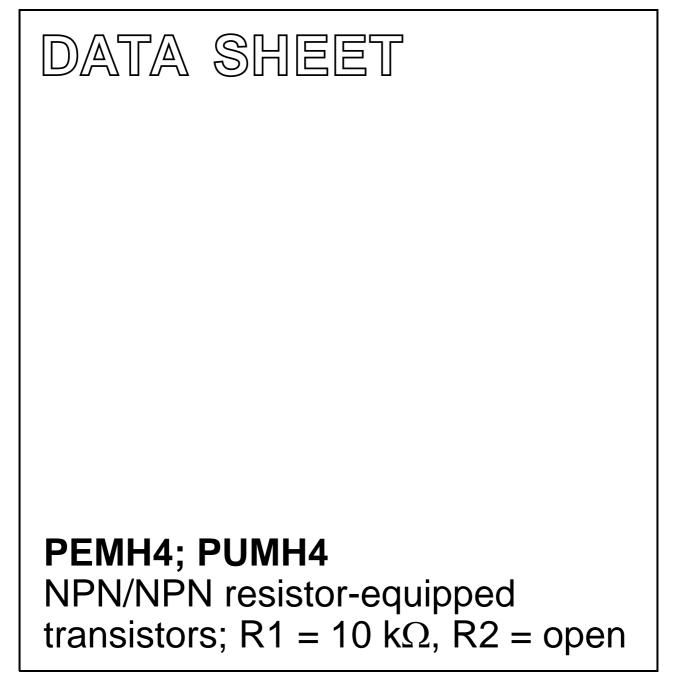
DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 2003 Oct 02 2004 Apr 14



### PEMH4; PUMH4

#### FEATURES

- · Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

#### APPLICATIONS

- Low current peripheral driver
- Replacement of general purpose transistors in digital applications
- Control of IC inputs.

#### DESCRIPTION

NPN/NPN resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

#### PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE			NPN/PNP	PNP/PNP COMPLEMENT	
	PHILIPS	EIAJ		COMPLEMENT		
PEMH4	SOT666	-	H4	PEMD4	PEMB4	
PUMH4	SOT363	SC-88	H*4	PUMD4	PUMB4	

#### Note

1. \* = p: Made in Hong Kong.

\* = t: Made in Malaysia.

#### SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL		PINNING		
	SIMPLIFIED OUTLINE AND STMBOL	PIN	DESCRIPTION		
PEMH4		1	emitter TR1		
PUMH4		2	base TR1		
		3	collector TR2		
		4	emitter TR2		
		5	base TR2		
		6	collector TR1		
	Top view MAM453				

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	_	50	V
lo	output current (DC)	-	100	mA
TR1	NPN	-	_	-
TR2	NPN	_	_	-
R1	bias resistor	10	_	kΩ
R2	bias resistor	open	_	-

### PEMH4; PUMH4

#### **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE			
ITFE NUMBER	NAME	DESCRIPTION	VERSION		
PEMH4	<ul> <li>Plastic surface mounted package; 6 leads</li> </ul>		SOT666		
PUMH4	<ul> <li>Plastic surface mounted package; 6 leads</li> </ul>		SOT363		

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transist	or		·	·	
V <sub>CBO</sub>	collector-base voltage	open emitter	-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	5	V
I <sub>O</sub>	output current (DC)		_	100	mA
I <sub>CM</sub>	peak collector current		_	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363	note 1	_	200	mW
	SOT666	notes 1 and 2	_	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Тj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C
Per device					
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363	note 1	_	300	mW
	SOT666	notes 1 and 2	-	300	mW

#### Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.

2. Reflow soldering is the only recommended soldering method.

### PEMH4; PUMH4

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or			
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$		
	SOT363	note 1	416	K/W
	SOT666	notes 1 and 2	416	K/W

#### Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.

2. Reflow soldering is the only recommended soldering method.

#### CHARACTERISTICS

 $T_{amb}$  = 25 °C unless otherwise specified.

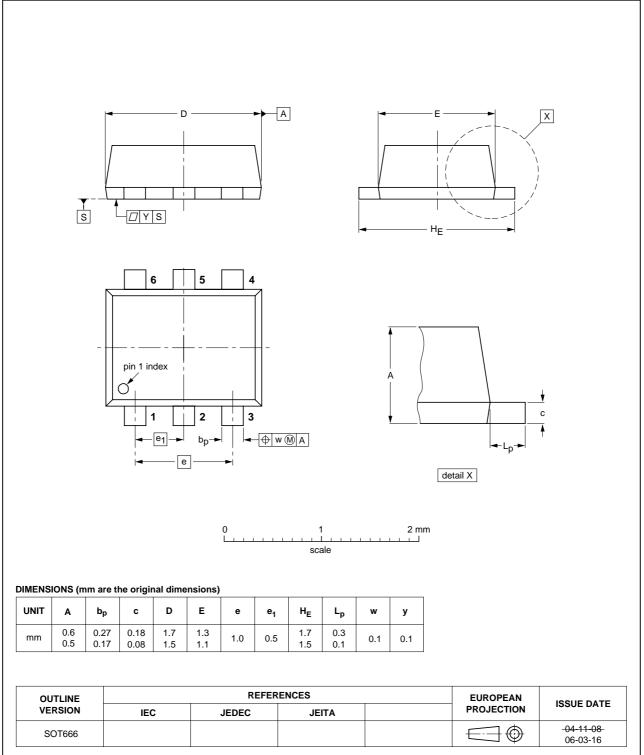
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Per transis	Per transistor						
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; \text{ I}_{E} = 0$	_	_	100	nA	
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0	-	-	1	μA	
		$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0; \text{ T}_{j} = 150 ^{\circ}\text{C}$	-	-	50	μA	
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 V; I_{C} = 0$	-	-	100	nA	
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; \text{ I}_{C} = 1 \text{ mA}$	200	-	-		
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA	-	-	150	mV	
R1	input resistor		7	10	13	kΩ	
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; \text{ I}_{E} = \text{i}_{e} = 0; \text{ f} = 1 \text{ MHz}$	-	-	2.5	pF	

**SOT666** 

### NPN/NPN resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = open

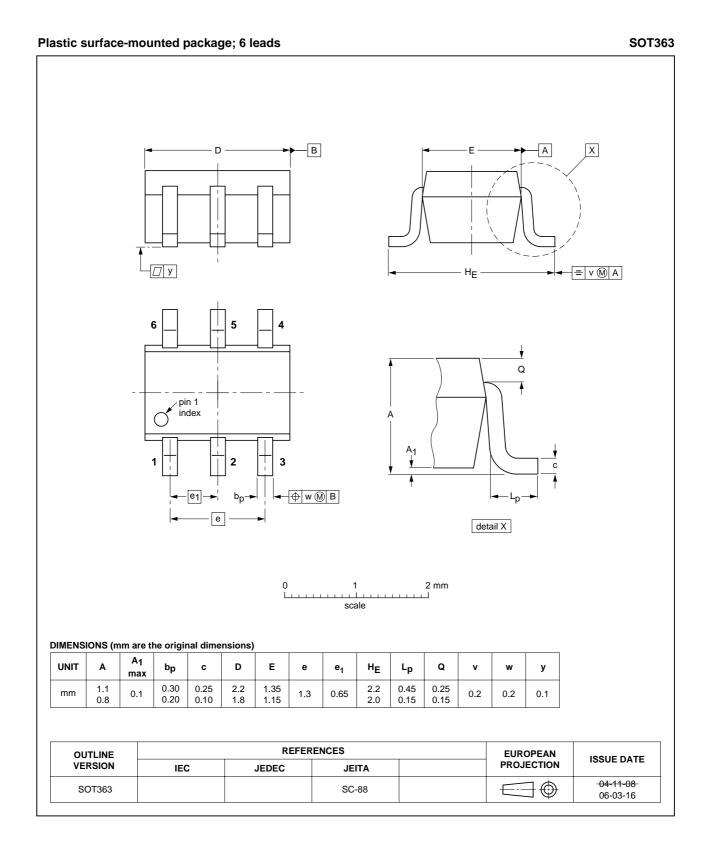
#### PACKAGE OUTLINE





PEMH4; PUMH4

### PEMH4; PUMH4



### PEMH4; PUMH4

#### DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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### **NXP Semiconductors**

#### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

#### **Contact information**

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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